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**(54) Circuit board adhesives for soldering environments**

(57) Disclosed is a method of bonding integrated circuit chips to lead frames where the leads are later soldered. A solution of an adhesive polyimide is used. The polyimide is the reaction product of an aromatic dianhydride and a mixture of an aromatic diamine and an aliphatic diamine.

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**Description**

This invention relates to a polyimide adhesive that is useful in bonding integrated circuit chips to a lead frame, where the leads are subsequently soldered. In particular, it relates to a solution of a polyimide made from a dianhydride and a mixture of an aromatic diamine and an aliphatic diamine.

In manufacturing microelectronic components, integrated circuit clips are bonded to lead frames using a polyimide resin. Later, the leads from the chips are soldered to the leads from the lead frames. A persistent problem in the industry has been the failure of the solder to "wet" the leads and form a good electrical connection.

We have discovered that the failure of solder to "wet" leads is due to the use of polyimide adhesive resins that contain siloxane groups. We have found that when these resins are heated, they evolve silicon-containing compounds that condense on the leads, preventing the solder from wetting the leads. We have further found that a polyimide adhesive made from a dianhydride and a mixture of aromatic and aliphatic diamines is an excellent adhesive for this application and will not prevent the solder from wetting the leads because it evolves almost no volatiles during bonding.

Surprisingly, we have also found that the peel strength after pressure cooking of the adhesives of this invention is better than for identical adhesives made with a siloxane-containing diamine instead of an aliphatic diamine.

The adhesives of this invention are prepared by reacting in an organic solvent an aromatic dianhydride with a mixture of aromatic and aliphatic diamines.

**Organic Solvent**

The organic solvent should be a low boiling solvent so that the adhesive can be dried at moderate temperatures; a boiling point of less than 180°C is preferred. Suitable organic solvents include N-methylpyrrolidone (NMP), dimethylacetamide (DMAC), 2-vinyl pyrrolidone, acetone, benzene, toluene, xylene, "Cellosolve" (glycol ethyl ether), "Cellosolve acetate" (hydroxyethyl acetate glycol monoacetate), diethyl ether, dichloromethane, dimethyl formamide (DMF), ethyl alcohol, methyl isobutyl ketone, methyl ethyl ketone, sulfolane, dimethyl sulfoxide (DMSO), hexamethylphosphoramide (HMPA), tetramethyl urea (TMU), diethyleneglycol diethyl ether, 1,2-dimethoxyethane (monoglyme), diethylene glycol dimethyl ether (diglyme), 1,2-bis(2-methoxyethoxy) ethane (triglyme), bis [2-(2-methoxyethoxy) ethyl] ether (tetraglyme), bis(2-methoxyethyl) ether tetrahydrofuran, m-dioxane, and p-dioxane. NMP and DMAC are preferred as they are good solvents for polyamic acids. About 5 to about 50 wt% (based on total solvent weight) of a cosolvent, such as toluene or xylene, may be useful with NMP, DMAC, or other solvents to aid in water removal.

**Aromatic Dianhydride**

Any aromatic dianhydride or combination of aromatic dianhydrides can be used as the dianhydride monomer in forming the polyimide. Examples of suitable aromatic dianhydrides include:

1,2,5,6-naphthalene tetracarboxylic dianhydride;  
 1,4,5,8-naphthalene tetracarboxylic dianhydride;  
 2,3,6,7-naphthalene tetracarboxylic dianhydride;  
 2-(3',4'-dicarboxyphenyl) 5,6-dicarboxybenzimidazole dianhydride;  
 2-(3',4'-dicarboxyphenyl) 5,6-dicarboxybenzoxazole dianhydride;  
 2-(3',4'-dicarboxyphenyl) 5,6-dicarboxybenzothiazole dianhydride;  
 2,2',3,3'-benzophenone tetracarboxylic dianhydride;  
 2,3,3',4'-benzophenone tetracarboxylic dianhydride;  
 3,3',4,4'-benzophenone tetracarboxylic dianhydride (BTDA);  
 2,2',3,3'-biphenyl tetracarboxylic dianhydride;  
 2,3,3',4'-biphenyl tetracarboxylic dianhydride;  
 3,3',4,4'-biphenyl tetracarboxylic dianhydride (BPDA);  
 bicyclo-[2,2,2]-octen-(7)-2,3,5,6-tetracarboxylic-2,3,5,6-dianhydride;  
 thio-diphthalic anhydride;  
 bis (3,4-dicarboxyphenyl) sulfone dianhydride,  
 bis (3,4-dicarboxyphenyl) sulfoxide dianhydride;  
 bis (3,4-dicarboxyphenyl oxadiazole-1,3,4) paraphenylenedianhydride,  
 bis (3,4-dicarboxyphenyl) 2,5-oxadiazole 1,3,4-dianhydride;  
 bis 2,5-(3',4'-dicarboxydiphenylether) 1,3,4-oxadiazole dianhydride;  
 bis (3,4-dicarboxyphenyl) ether dianhydride or 4,4'-oxydiphthalic anhydride (ODPA);  
 bis (3,4-dicarboxyphenyl) thioether dianhydride;  
 bisphenol A dianhydride (BPADA);

bisphenol S dianhydride;  
 2,2-bis (3,4-dicarboxyphenyl) hexafluoropropane dianhydride or 5,5-[2,2,2-trifluoro-1-(trifluoromethyl)ethylidene] bis-1,3-isobenzofurandione) (6FDA);  
 hydroquinone bisether dianhydride;  
 5 bis (3,4-dicarboxyphenyl) methane dianhydride;  
 cyclopentadienyl tetracarboxylic acid dianhydride;  
 cyclopentane tetracarboxylic dianhydride;  
 ethylene tetracarboxylic acid dianhydride;  
 perylene 3,4,9,10-tetracarboxylic dianhydride;  
 10 pyromellitic dianhydride (PMDA);  
 tetrahydrofuran tetracarboxylic dianhydride; and resorcinol dianhydride.

The preferred dianhydrides are BTDA, BPDA, ODPA, and 6FDA, as they are readily available and have been found to give superior properties. The dianhydrides can be used in their tetraacid form or as mono, di, tri, or tetra esters of the tetra acid, but the dianhydride form is preferred because it is more reactive.  
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#### Aromatic Diamine

To prevent the polyimide from being too soft, about 50 to about 95 mole % of the diamine content of the polyimide  
 20 should be a non-siloxane containing aromatic diamine; preferably, about 75 to about 90 mole % of the diamine content  
 is non-siloxane containing aromatic diamine. Examples of suitable aromatic diamines include:

m-phenylenediamine;  
 p-phenylenediamine (PDA);  
 25 2,5-dimethyl-1,4-diaminobenzene or 2,5-dimethyl-1,4-phenylenediamine (DPX);  
 2,4-diaminotoluene (TDA);  
 2,5- and 2,6-diaminotoluene;  
 p- and m-xylenediamine;  
 4,4'-diaminobiphenyl;  
 30 4,4'-diaminodiphenyl ether or 4,4'-oxydianiline (ODA);  
 4,4'-diaminobenzophenone;  
 3,3',3,4', or 4,4'-diaminophenyl sulfone or m,m-, m,p- or p,p- sulfone dianiline;  
 4,4'-diaminodiphenyl sulfide;  
 3,3' or 4,4'-diaminodiphenylmethane or m,m- or p,p-methylene dianiline;  
 35 3,3'-dimethylbenzidine;  
 α,α'-bis(4-aminophenyl)-1,4-diisopropyl benzene or 4,4'-isopropylidenedianiline or bisaniline p;  
 α,α'-bis(4-aminophenyl)-1,3-diisopropyl benzene or 3,3'-isopropylidenedianiline or bisaniline m;  
 1,4-bis(p-aminophenoxy)benzene;  
 1,3-bis(p-aminophenoxy)benzene;  
 40 4,4'-bis(4-aminophenoxy)biphenyl;  
 1,3-bis(3-aminophenoxy)benzene (APB);  
 2,4-diamine-5-chlorotoluene;  
 2,4-diamine-6-chlorotoluene;  
 2,2-bis(4[4-aminophenoxy]phenyl)propane (BAPP);  
 45 trifluoromethyl-2,4-diaminobenzene;  
 trifluoromethyl-3,5-diaminobenzene;  
 2,2'-bis(4-aminophenyl)-hexafluoropropane (6F diamine);  
 2,2'-bis(4-phenoxy aniline) isopropylidene;  
 2,4,6-trimethyl-1,3-diaminobenzene;  
 50 4,4'-diamino-2,2'-trifluoromethyl diphenyloxide;  
 3,3'-diamino-5,5'-trifluoromethyl diphenyloxide;  
 4,4'-trifluoromethyl-2,2'-diaminobiphenyl;  
 2,4,6-trimethyl-1,3-diaminobenzene;  
 diaminoanthraquinone;  
 55 4,4'-oxybis[2-trifluoromethyl]benzeneamine] (1,2,4-OBABTF);  
 4,4'-oxybis[3-trifluoromethyl]benzeneamine];  
 4,4'-thiobis[(2-trifluoromethyl)benzeneamine];  
 4,4'-thiobis[(3-trifluoromethyl)benzeneamine];

- 4,4'-sulfoxybis[(2-trifluoromethyl)benzeneamine];  
 4,4'-sulfoxybis[(3-trifluoromethyl)benzeneamine];  
 4,4'-ketobis[(2-trifluoromethyl)benzeneamine];  
 4,4'-[{(2,2,2-trifluoromethyl)-1-(trifluoromethyl)-ethylidine}bis(3-trifluoromethyl)benzeneamine].

5       The preferred aromatic diamines are APB, BAPP, DPX, and bisaniline P, or a combination of these, due to their excellent properties.

#### Aliphatic Diamines

10     About 5 to about 50 mole% of the diamine monomer, and preferably about 10 to about 25 mole%, is an aliphatic diamine that does not contain siloxane groups. If less aliphatic diamine is used, the polyimide becomes less soluble, has less adhesion, and is more difficult to process, and more aliphatic diamine will lower the Tg. The aliphatic diamines useful in this invention preferably have the formula H<sub>2</sub>N-R-NH<sub>2</sub> where R is hydrocarbon from C<sub>2</sub> to C<sub>20</sub>; preferably R is  
 15     a straight chain hydrocarbon from C<sub>6</sub> to C<sub>12</sub> as those diamines are more readily available. Also, the aliphatic diamine preferably is an α, ω-diamine because they are more reactive. Examples of suitable aliphatic diamines include:

- hexamethylenediamine or 1,6-hexanediamine (HD);  
 heptamethylene diamine;  
 20     monomethylenediamine;  
 decamethylenediamine;  
 1,12-dodecamethylenediamine (DDD);  
 2-methyl-1,5-pentanediamine (MDP);  
 1,4-cyclohexanediamine; and  
 25     bis(4-aminocyclohexyl) methane.

The preferred aliphatic diamine is DDD because it has been found to work well.

#### Preparation of Polyimide

30     Generally, stoichiometric quantities of diamine and dianhydride monomers are used to obtain polyimides of the highest molecular weight, but the equivalent ratio of dianhydride to diamine can range from 1:2 to 2:1. The solution of the monomers in the solvent is preferably about 5 to about 20 wt% solids, where "solids" means components other than the solvent.

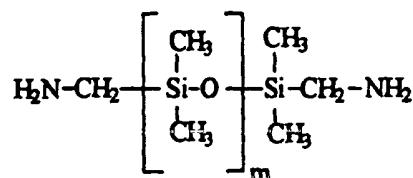
35     Upon the addition of the monomers to the solvent, polymerization will occur at room temperature to form a polyamic acid. The polyamic acid is then imidized. This can be accomplished chemically by, for example, the addition of acetic anhydride, or by heating, preferably at about 130 to about 200°C. The polyimide is preferably fully imidized.

The solution of the polyimide is spread on a non-adhering surface, such as glass coated with a release agent, and heated at 250°C to remove solvent. The resulting film is peeled from the surface and is positioned between surfaces to  
 40     be bonded. Bonding can also be done by applying the solution to a surface, drying by evaporating the solvent, and covering the polyimide with a second surface. Also, a paste of 30 to 70 wt% polyimide in an organic solvent, which also contains about 1 to about 10 wt% of a thixotropic, such as silica, can be screen printed onto one of the articles to be bonded. Bonding can be achieved by heating at about 250 to about 450°C for less than a second.

The following examples further illustrate this invention.

#### Example 1

45     Various polyamic acids were prepared in a solvent mixture of 85 wt% NMP-15 wt% toluene by adding monomers at 17 wt% solids to the solvent mixture and letting the resulting solution stand at room temperature for 16 hours. This  
 50     was followed by imidization at 165 to 175°C for 2 to 4 hours. Formulations 1 to 4 and 6 to 9 are comparative examples ("C") as they contain siloxane diamines. The siloxane diamines have the formula:



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and are designated "G<sub>m</sub>". The following table gives the formulations prepared and their Tg as determined by dynamic mechanical thermal analysis (DMTA):

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Formulation	Aromatic Dianhydride (m)	Aromatic Diamine (m)	Aliphatic Diamine (m)	Siloxane Diamine (m)	Tg (°C)
1C	BPDA (0.0215)	BAPP (0.0205)		G <sub>9</sub> (0.0031)	239
	BTDA (0.0092)	DPX (0.0063)		G <sub>1</sub> (0.0016)	
2C	BPDA (0.1031)	BAPP (0.0949)	DDD (0.0092)	G <sub>1</sub> (0.0072)	247
	BTDA (0.0427)	DPX (0.0292)		G <sub>25</sub> (0.0053)	
3C	BPDA (0.1031)	BAPP (0.0949)	DDD (0.0161)	G <sub>25</sub> (0.0055)	247
	BTDA (0.0427)	DPX (0.0292)			
4C	BPDA (0.1031)	BAPP (0.0949)		G <sub>1</sub> (0.00167)	244
	BTDA (0.0427)	DPX (0.0292)		G <sub>25</sub> (0.0050)	
5	BPDA (0.1031)	BAPP (0.0949)	DDD (0.0217)		242
	BTDA (0.0427)	DPX (0.0292)			
6C	ODPA (0.1758)	APB (0.1023)	DDD (0.0210)	G <sub>25</sub> (0.0118)	163
7C	ODPA (0.1365)	APB (0.1122)		G <sub>25</sub> (0.0143)	176
8C	ODPA (0.1357)	APB (0.1025)		G <sub>1</sub> (0.0217)	157
				G <sub>25</sub> (0.0115)	
9C	ODPA (0.0333)	APB (0.0250)		G <sub>9</sub> (0.0083)	148
10	ODPA (0.1727)	APB (0.1296)	DDD (0.0431)		162
11	ODPA (0.1727)	APB (0.1345)	MPD (0.0447)		187
12	ODPA (0.1727)	APB (0.1345)	HD (0.0447)		182

The formulations were tested for peel strength as bonded and after one and two days at 121°C and 100% relative humidity (RH) (pressure cooker test). The bond was for 60 seconds at 3.4 MPa (500 psi) to Alloy 42 (an alloy of 42 wt% nickel and 58 wt% iron). Samples of formulations were placed in a thermal desorber-gas chromatograph. The samples were heated to 400°C for about 5 minutes and the wt% of siloxane-containing volatiles emitted was determined. The following table gives the results:

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Formulation	Bond Temp. (°C)	PEEL STRENGTH (kg/cm)			Wt% Siloxane Volatiles (ppm)*
		Initial	After 1 day 121°C/100% RH	After 2 days 121°C/100% RH	
1C	275	1.20	1.47	0.99	2500
2C	275	0.93	0.77	0.71	2060
3C	275	0.94	0.78	0.72	1990
4C	275	1.06	0.81	0.67	2500
5	275	1.73	1.80	1.67	0
6C	250	1.49	0	0	4200
7C	250	0.64	0	0	4910
8C	250	1.39	0	0	4660
9C	250	1.84	0.16	0	5000
10	225	1.89	0.90	1.46	0
11	250	1.80	1.87	1.70	0
12	250	1.97	1.96	1.70	0

c = comparative example

\*based on wt of polymer

The above table shows that the best retention of peel strength was in the formulations of this invention, formulations 5, 10, 11, and 12.

### Claims

1. An improved method of bonding an integrated circuit chip to a lead frame without adversely affecting soldering of the leads of said chip to said frame comprising
  - (A) placing between said integrated circuit chip and said lead frame and in contact therewith a polyimide adhesive which comprises the reaction product of
    - (1) at least one aromatic dianhydride; and
    - (2) diamine which is a mixture of
      - (a) about 50 to about 95 mole % of at least one aromatic diamine; and
      - (b) about 5 to about 50 mole % aliphatic diamine, where said polyimide adhesive is free of siloxane linkages; and
  - (B) heating then cooling said polyimide to form a bond between said integrated circuit chip and said lead frame.
2. A method according the Claim 1 wherein said polyimide is fully imidized.
3. A method according to Claim 1 or 2 wherein said aromatic dianhydride is selected from 3,3',4,4'-benzophenone tetracarboxylic dianhydride, 3,3',4,4'-biphenyl tetracarboxylic dianhydride, oxydiphtalic dianhydride, and 5,5-[2,2,2-trifluoro-1-(trifluoromethyl)ethylidene]bis-1,3-isobenzofurandione.
4. A method according to any of Claims 1 to 3 wherein said aromatic diamine is selected from 1,3-bis(3-aminophenoxy) benzene, 2,2-bis(4[4-aminophenoxy]phenyl) propane, 2,5-dimethyl-1,4-diamonobenzene, and bisaniline P.
5. A method according to any of Claims 1 to 4 wherein said aliphatic diamine is from C<sub>2</sub> to C<sub>20</sub>.

6. A method according to any of Claims 1 to 5 wherein said aliphatic diamine is an  $\alpha,\omega$ -diamine.
7. A method according to any of Claims 1 to 6 wherein a film is formed by evaporating solvent from a solution of said polyimide and said film is placed between said chip and said lead frame.
- 5 8. A method according to Claim 7 wherein said solvent is selected from the group consisting of N-methyl pyrrolidone and dimethylacetamide.
9. A method according to Claim 1 wherein a paste containing said polyimide is screen printed onto said lead frame.
- 10 10. A method according to Claim 1 wherein said aromatic dianhydride is selected from the group consisting of 3,3',4,4'-benzophenone tetracarboxylic dianhydride, 3,3',4,4'-biphenyl tetracarboxylic dianhydride, and oxydiphtalic dianhydride, said aromatic diamine is selected from the group consisting of 1,3-bis(3-aminophenoxy) benzene, 2,2-bis(4[4-aminophenoxy]phenyl) propane, 2,5-dimethyl-1,4-diamonobenzene, and bisaniline P, and said aliphatic diamine is 1,12-dodecadiamine.
- 15 11. An article obtainable by the method of any of Claims 1 to 10.
12. An improved method of mounting an integrated circuit chip to a lead frame comprising
- 20 (A) screen printing onto said lead frame a paste which comprises about 30 to about 70 wt% of a fully imidized polyimide and about 1 to about 10 wt% of a thixotrope in an organic solvent, where said polyimide comprises the reaction product of
- 25 (1) at least one aromatic dianhydride;
- (2) diamine in a mole ratio of 1:2 to 2:1 with said aromatic dianhydride, said diamine comprising a mixture of
- 30 (a) about 75 to about 85 mole % of at least one aromatic diamine; and
- (b) about 15 to about 25 mole % aliphatic,  $\alpha,\omega$ -diamine from C<sub>6</sub> to C<sub>12</sub>, where said polyimide is free of siloxane linkages;
- 35 (B) evaporating said solvent;
- (C) placing said chip in contact with said paste on said lead frame;
- (D) heating then cooling said paste; and
- (E) soldering the leads of said integrated circuit chip to said lead frame.
13. A method according to Claim 12 wherein said aliphatic  $\alpha,\omega$ -diamine is 1,12-dodecadiamine.
- 40 14. A method according to Claim 12 or 13 wherein said aromatic dianhydride is selected from 3,3',4,4'-benzophenone tetracarboxylic dianhydride, 3,3',4,4'-biphenyl dianhydride, and oxydiphtalic dianhydride.
15. A method according to any of Claims 12 to 14 wherein said aromatic diamine is selected from 1,3-bis(3-aminophenoxy) benzene, 2,2-bis(4[4-aminophenoxy]phenyl) propane, 2,5-dimethyl-1,4-diamonobenzene, and bisaniline P.
- 45 16. A method according to Claim 12 wherein said aromatic dianhydride is selected from 3,3',4,4'-benzophenone tetracarboxylic dianhydride, 3,3',4,4'-biphenyl tetracarboxylic dianhydride, and oxydiphtalic dianhydride, said aromatic diamine is selected from 1,3-bis(3-aminophenoxy) benzene, 2,2-bis(4[4-aminophenoxy]phenyl) propane, 2,5-dimethyl-1,4-diamonobenzene, and bisaniline P, and said aliphatic diamine is 1,12-dodecadiamine.
- 50 17. A method according to any of Claims 12 to 16 wherein said solvent is selected from the group consisting of N-methyl pyrrolidone and dimethylacetamide.
18. An article obtainable by the method of any of Claims 12 to 17.
- 55 19. A method of mounting an integrated circuit chip onto a lead frame comprising
- (A) placing between said integrated circuit chip and said lead frame in contact therewith polyimide adhesive

which comprises the reaction product of

- (1) at least one aromatic dianhydride; and
- (2) diamine which is a mixture of

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- (a) about 50 to about 95 mole% of at least one aromatic diamine; and
- (b) about 5 to about 50 mole% aliphatic diamine, where said polyimide is free of siloxane linkages;

and.

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- (B) heating then cooling said polyimide to form a bond between said integrated circuit chip and said lead frame; and
- (C) soldering the leads of said integrated circuit chip to said lead frame.

**20. An article obtainable by the method of Claim 19.**

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Office

## EUROPEAN SEARCH REPORT

Application Number

EP 98 10 0626

DOCUMENTS CONSIDERED TO BE RELEVANT			CLASSIFICATION OF THE APPLICATION (Int.Cl.6)						
Category	Citation of document with indication, where appropriate, of relevant passages	Relevant to claim							
A	DE 195 40 306 A (SAMSUNG ELECTRONICS CO., LTD)  * claim 1 * ---	1,7,9, 11,12, 18-20	C09J179/08 C08G73/10 H01L23/495						
A	HSIAO B S ET AL: "CRYSTALLINE HOMOPOLYIMIDES AND COPOLYIMIDES DERIVED FROM 3,3',4,4'-BIPHENYLTETRACARBOXYLIC DIANHYDRIDE/1,3-BIS(4-AMINOPHOENOXY)BENZENE/1,12-DODECA NEDIAMINE. 2 CRYSTALLIZATION, MELTING, AND MORPHOLOGY" MACROMOLECULES, vol. 29, no. 1, 1 January 1996, pages 135-142, XP000543000 ----	1-6,8, 10,13-17							
			TECHNICAL FIELDS SEARCHED (Int.Cl.6)						
			C09J C08G H01L						
<p>The present search report has been drawn up for all claims</p> <table border="1" style="width: 100%; border-collapse: collapse;"> <tr> <td style="width: 33%;">Place of search</td> <td style="width: 33%;">Date of completion of the search</td> <td style="width: 34%;">Examiner</td> </tr> <tr> <td>THE HAGUE</td> <td>20 April 1998</td> <td>Glanddier, A</td> </tr> </table> <p>CATEGORY OF CITED DOCUMENTS</p> <p>X : particularly relevant if taken alone      Y : particularly relevant if combined with another document of the same category      A : technological background      O : non-written disclosure      P : intermediate document</p> <p>T : theory or principle underlying the invention      E : earlier patent document, but published on, or after the filing date      D : document cited in the application      L : document cited for other reasons      &amp; : member of the same patent family, corresponding document</p>				Place of search	Date of completion of the search	Examiner	THE HAGUE	20 April 1998	Glanddier, A
Place of search	Date of completion of the search	Examiner							
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# EUROPEAN PATENT OFFICE

## Patent Abstracts of Japan

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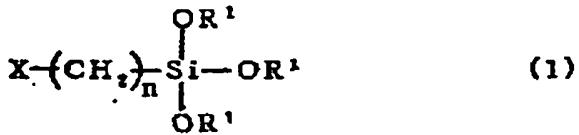
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APPLICATION NUMBER : 2000315940

APPLICANT : HITACHI CHEM CO LTD;

INVENTOR : TAKEDA SHINJI;

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C09J183/04 C09J183/07 H01L 21/52

TITLE : ADHESIVE FILM, ITS  
MANUFACTURING METHOD AND  
SEMICONDUCTOR DEVICE HAVING  
ADHESIVE FILM



ABSTRACT : PROBLEM TO BE SOLVED: To provide an adhesive film which bonds an electronic part such as a semiconductor element to a lead frame and an insulating support substrate and has high adhesion at a high temperature, low stress properties, and low temperature adhesion with or without a substrate, a method for manufacturing the film, and a semiconductor device using the film.

SOLUTION: The method for manufacturing the adhesive film comprises steps of (I) mixing 100 pts.wt. polyimide resin, 0.01-50 pts.wt. silane coupling agent to be represented by the formula (wherein X is a vinyl, amino, glycidoxyl, methacryloxy, mercapto or isocyanate group; n is 1-10; and R1 is a 1-10C alkyl group), 0-200 pts.wt. thermosetting resin, and 0-8,000 pts.wt. filler in an organic solvent, (II) coating the resulting mixed fluid on a substrate, and (III) heating and drying the coated film. A semiconductor element is obtained by bonding a support member having the above adhesive film to the back surface of a semiconductor. The semiconductor device has an electronic part to which the semiconductor element has been bonded.

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